



# Electronic structure and vibrational properties in cobalt-based full-Heusler compounds: A first principle study of $\text{Co}_2\text{MnX}$ ( $X = \text{Si, Ge, Al, Ga}$ )

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## ABSTRACT

First-principles self-consistent pseudopotential plane wave calculations based on density functional theory were performed in order to study magnetic moments, density of states and half-metallicity of  $\text{L}_{21}$  type full Heusler alloys with formula  $\text{Co}_2\text{MnX}$  ( $X = \text{Si, Ge, Al, Ga}$ ). Half-metallicity in terms of total spin-moments was discussed since perfect half-metals show Slater–Pauling (SP) behavior. The effects of the atomic number on the lattice constants, the bulk moduli and the Curie temperatures were shown. The magnetic moments were calculated, while slight deviations of about  $0.06\text{--}0.16 \mu_B$  were found for  $\text{Co}_2\text{MnAl}$  and  $\text{Co}_2\text{MnGa}$ , the  $\text{Co}_2\text{MnSi}$  and  $\text{Co}_2\text{MnGe}$  have been found to be half metals. Mechanical stability of these compounds has been analyzed in terms of their elastic constants. The size of the gap in the minority states and the position of  $E_F$  inside the gap was also discussed as it is an important factor for the application of half-metallic ferromagnetic alloys. Finally, phonon dispersion curves and the density of states were calculated by employing the density-functional perturbation theory and discussed.

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## 1. Introduction

Half-metallic ferromagnetic alloys (HMFs) are presently under intense investigation [1–6]. They show mixture properties of metal and semiconductor. They are fully spin polarized around Fermi energy level ( $E_F$ ): while one spin projection has metallic character at  $E_F$ , the other spin projection demonstrates semiconductor-like character [7]. Recently, HMFs have attracted attention since they show great potential for spintronics such as tunneling magnetoresistance (TMR) and giant magnetoresistance (GMR) elements [1] and also for electro-mechanical [8] applications.

Full-Heusler alloys, such as  $\text{Co}_2\text{MnSi}$ ,  $\text{Co}_2\text{MnGe}$ , gained a particular interest and became most widely studied in this field due to their high Curie temperatures, a requirement for integration into devices [9]. They have been predicted from first-principles to be half metallic and potential candidates for spintronic applications. However, spin polarizations of only 50–60% were experimentally obtained for these compounds, a decrease attributed to defects in the Mn and Co sublattices [10–13] and to thermally excited magnons [14]. One of the most attractive features of Heusler compounds is the possibility to tune their magnetic properties, such

as  $M_s$  [15,16],  $T_c$  [17], and Fermi level position [9,18], using the chemical handle provided by the number of valence electrons  $Z_v$ . The Heusler compounds are well known to be systematized by the number of valence electrons  $Z_v$ . Striking examples are the magnetic moment described by the Slater–Pauling rule (SP rule) [2,19,20] or the Curie temperature  $T_c$  [17], which are both generally proportional to  $Z_v$ . A second advantage of Heusler alloys for realistic applications is their structural similarity to the zinc-blende structure, adopted by binary semiconductors widely used in industry (such as GaAs and ZnS).

Among the predicted half-metallic ferromagnets, the  $\text{Co}_2\text{MnX}$  (with  $X = \text{Si, Ge, Ga, Al}$ ) full-Heusler family with  $\text{L}_{21}$  structure is regarded as one of the most promising candidates for a high efficiency TMR device [21,22] because of its ideal 100% spin polarization for ( $\text{Co}_2\text{MnSi}$  and  $\text{Co}_2\text{MnGe}$ ) at the Fermi level, a good structural matching with main stream semiconductors (in terms of lattice constants and crystal structure) and very high Curie temperatures [1,11] about 900 K, while for the other compounds the Curie temperature is near room temperature. Recently, it has been found that several  $\text{Co}_2\text{MnZ}$  Heusler alloys had high spin polarizations more than 85% [5,14], much higher than 3d transition metals and their alloys, which typically have spin polarizations of about 45% or lower [23,24].

Generally, the full-Heusler alloys show a Slater–Pauling behavior and the total spin-magnetic moment per unit cell ( $M_t$ ) scales with the total number of valence electrons ( $Z_t$ ) following the rule:

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$M_t = Z_t - 24$ . As a result half-metallic ferromagnets, such as the Heusler compounds with formula  $X_2YZ$ , are expected to show an integer value for the spin magnetic moment. This latter quantity is an important characteristic property for these systems in stoichiometric compositions. The small deviations from integer magnetic moment would lead to significant disruptions in half-metallic character by non-zero electronic density of states for minority spins around Fermi level [25]. In contrast to experiments, calculations give noninteger values in certain cases where the compounds are based on Co which is our case for  $\text{Co}_2\text{MnGa}$  and  $\text{Co}_2\text{MnAl}$ . Webster studied the chemical and magnetic structures of the alloys  $\text{Co}_2\text{MnX}$  ( $X = \text{Al, Ga, Si, Ge, Sn}$ ) and reported [26] that the alloys with  $X = \text{Si, Ge}$  and  $\text{Sn}$  had net moments of approximately  $5.1 \mu_B$  per molecule with individual moments of  $0.75 \mu_B$  and  $3.6 \mu_B$  on Co and Mn sites, respectively, and that the alloys containing Al or Ga have net moments of approximately  $4.0 \mu_B$  per molecule and correspondingly smaller moments on both Co and Mn sites [26]. In addition, for  $\text{Co}_2\text{MnSi}$ , a Curie temperature of  $T_c = 985 \text{ K}$  and a total magnetic moment of about  $5 \mu_B$  [21,27,28] have been measured.

The knowledge of the basic magnetic, electronic and vibrational properties of these materials, is required in order to fully exploit these promising materials, to design new generation spin-dependent devices, to understand their underlying electronic structure and to establish structure–property relationships. In the present work, by means of a DFT approach we examined the series of Heusler alloys  $\text{Co}_2\text{MnX}$  (with  $X = \text{Si, Ge, Al, Ga}$ ) assuming they crystallize in the typical  $L2_1$  structure. We find that, while there have been a number of works focused on the electronic and magnetic properties of these alloys, there has been little effort, to the best of our knowledge, to investigate these system in term of their elastic and phonon properties. We derived magnetic and electronic properties as well as vibrational and elastic properties for all of these compounds, and we also investigated the influence of  $X$  atomic number on the electronic structure.

In Section 2, we report some details about the crystal structure and the numerical values. We concentrate on the equilibrium lattice constant, bulk modulus and magnetic moments in Section 3.1. We focus on the elastic properties in Section 3.2 and discuss the electronic properties in terms of band structures and density of states, and we analyze the vibrational properties in Section 3.3, and finally, we draw conclusions in Section 4.

## 2. The crystal structure and calculational details

Heusler compounds are good candidates for spintronic materials since they combine high Curie temperatures and coherent growth on top of semiconductors [2,29].  $-X_2YZ$  Heusler compounds crystallize in the  $L2_1$  structure (see Fig. 1), they consist of four fcc sublattices with each one occupied by a single chemical element at  $A(0,0,0)$ ,  $C(1/2,1/2,1/2)$ ,  $B(1/4,1/4,1/4)$ , and  $D(3/4,3/4,3/4)$  positions. They belong to the  $Fm\bar{3}m$  space group. In general,  $X$  and  $Y$  atoms are transition metals and  $Z$  is a main group element. In the compound  $\text{Co}_2\text{MnX}$  (with  $X = \text{Si, Ge, Al, Ga}$ ) each Mn or sp atom has eight Co atoms as first neighbors sitting in an octahedral symmetry position, while each Co has four Mn and four sp atoms as first neighbors and thus the symmetry of the crystal is reduced to the tetrahedral one.

The first-principles studies of the  $\text{Co}_2\text{MnX}$  (with  $X = \text{Si, Ge, Al, Ga}$ ) Heusler compounds are performed by employing the self-consistent ultrasoft pseudopotential method [30] based on the density functional theory. The exchange–correlation potential were described within the generalized gradient approximation (GGA) of Perdew–Burke–Ernzerhof (PBE) [31,32], incorporated into the quantum-Espresso code [33]. Nonmagnetic as well as

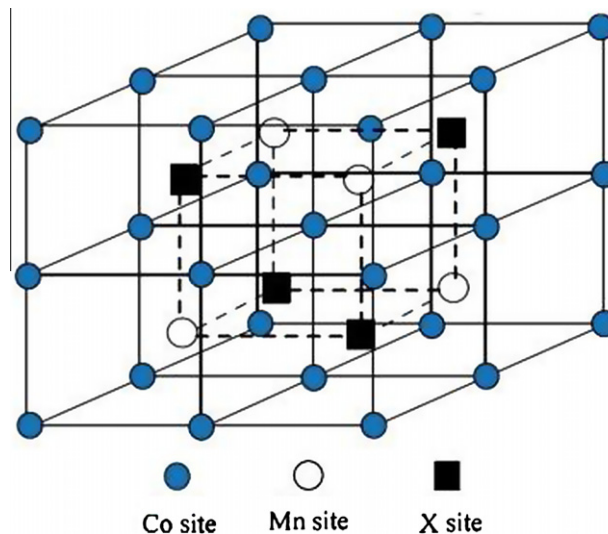


Fig. 1. The  $L2_1$  structure of Heusler alloys  $\text{Co}_2\text{MnX}$  ( $X = \text{Si, Ge, Al, Ga}$ ).

ferromagnetic orderings were considered. The energy cutoff for the expansion of the eigenfunctions was set to 40 Ry. The electronic charge density was evaluated up to the kinetic energy cut-off of 400 Ry. A grid of  $(10 \times 10 \times 10)$   $k$ -points generated was symmetry reduced and used to sample the irreducible wedge of the first Brillouin zone. Integration up to the Fermi surface was performed using the smearing technique [34] with smearing parameter  $\sigma = 0.02 \text{ Ry}$ . When exploring the electronic structure, a finer grid  $(35 \times 35 \times 35)$  was chosen to generate a high quality charge density. With these choices, the total energy is converged to 1 mRy per atom. Having obtained self-consistent solutions of Kohn–Sham equations, the lattice-dynamical properties were calculated within the framework of the self-consistent density functional perturbation theory [35]. To obtain complete phonon dispersions and density of states, eight dynamical matrices were calculated on a  $(4 \times 4 \times 4)$   $q$ -point mesh. The dynamical matrices at arbitrary wave vectors were evaluated using Fourier deconvolution on this mesh. The ground state of each compound was found by minimizing the total energy as a function of the lattice parameters.

## 3. Results and discussion

### 3.1. ground-state properties

We performed calculations of the electronic structures of four Co-based Heusler alloys with the generic formula  $\text{Co}_2\text{MnX}$  (with  $X = \text{Si, Ge, Al, Ga}$ ). It was found that the ferromagnetic spin-polarized configuration had a lower minimum total energy than that found in the paramagnetic non spin polarized case. The same behavior was observed in a previous work reported in ref. [36] that  $\text{Co}_2\text{MnZ}$  alloys, where  $Z$  is Si, Al, Ga, Sn, Sb, were ferromagnetic and had relatively large Curie temperatures compared to most other Mn-based Heusler alloys with  $L2_1$  structure. The volume optimization was performed using several lattice constants near the experimental ones. The calculated total energies within GGA as functions of the volume were fitted to Murnaghan's equation of state to obtain the ground-state properties [37].

In Table 1, we report our calculated equilibrium lattice constant, along with bulk modulus and the total magnetic moment, the density of states at the Fermi level ( $E_F$ ), compared with the available experimental and theoretical data [11,26,38–42]. The bulk

**Table 1**

Calculated lattice constant  $a$ , bulk modulus  $B$  and its pressure derivative  $B'$ , the total magnetic moment and the density of states at Fermi energy  $N(E_F)$  for  $\text{Co}_2\text{MnX}$  (with  $X = \text{Si, Ge, Al, Ga}$ ) full-Heusler, compared with the available experimental and theoretical data.

Material	Reference	$a_0$ (Å)	$B$ (GPa)	$B'$	$M_t$ ( $\mu_B$ )	$N(E_F)$ (states/eV cell)	
						$N(\uparrow, E_F)$	$N(\downarrow, E_F)$
$\text{Co}_2\text{MnSi}$	This work	5.633	212.8	4.680	5.00	1.17	0
	Exp [26]	5.654	–	–	5.07		
	Theoretical [11]	5.634	226	–	5.00		
	Theoretical [38]	5.643	–	–	5.00		
	Theoretical [39]	5.523	–	–	5.06		
	Theoretical [40]	5.639	214	4.674	5.00		
	[45]	–	–	–	–	0.31	
$\text{Co}_2\text{MnGe}$	This work	5.753	191.4	4.54	5.01	1.33	0
	Exp [26]	5.743	–	–	5.11		
	Theoretical [11]	5.734	188	–	5.00		
	Theoretical [39]	5.618	–	–	4.99		
	Theoretical [42]	5.729	–	–	4.99		
$\text{Co}_2\text{MnAl}$	This work	5.707	181.3	4.43	4.06	1.16	0.244
	Exp [26]	5.756	–	–	4.01		
	Theoretical [38]	5.695	–	–	4.04		
	Theoretical [39]	5.586	–	–	4.03		
$\text{Co}_2\text{MnGa}$	This work	5.724	186.7	–	4.16	1.7	0.381
	Exp [26]	5.770	–	–	4.05		
	Theoretical [39]	5.586	–	–	4.08		
	Theoretical [41]	5.724	199	–	4.08		
	Theoretical [42]	5.710	–	–	–		

modulus increases by 2.3% when we replace Al by Ga, however, it decreases when we substitute Ge for Si by about 11.18%. We mention that the bulk modulus of  $\text{Co}_2\text{MnSi}$  is the largest one of about 212.8 GPa, and as a result, it is predicted to be the hardest in the studied series.

Another important point is that in Heusler materials like the ones studied here the total spin moment should be an integer number since both the total number of valence electrons as well as the number of occupied minority states are integers. However our results in Table 1 do not give integer numbers for the total moments, but slight deviations of about 0.06–0.16  $\mu_B$  were found for  $\text{Co}_2\text{MnAl}$  and  $\text{Co}_2\text{MnGa}$ . As a matter of fact their total spin moments were found to be 4.06  $\mu_B$  and 4.16  $\mu_B$ , respectively, compared to the ideal 4  $\mu_B$  predicted by the SP rule while those of the Si and Ge-based alloys are exactly 5  $\mu_B$  as predicted by the SP rule and measured in previous works [21,27,28]. The total spin moment for  $\text{Co}_2\text{MnGe}$ , was found to be 5.01  $\mu_B$ , with a minute deviation that is possibly due to inaccuracies associated with the numerical integration. The magnetic moments are mainly due to the Mn atoms while the magnetic transition metal Co atoms also contribute to additional magnetic moments; this observation is consistent with a previous work reported in [14]. The Co atoms are ferromagnetically coupled to the Mn spin moments and they possess a spin moment that varies from 0.7 to 1.0  $\mu_B$ , while the sp atom has a very small negative moment which is an order of magnitude smaller than the Co moment. The replacement of Al or Ga by Si or Ge in Co-based alloys leads to substantial increase of magnetic moment from 4 to 5 whereas the replacement of Al by Ga or Si by Ge does not change the value of total magnetic moment.

The Curie temperatures  $T_c$  for  $\text{Co}_2\text{MnX}$  (with  $X = \text{Si, Ge, Al, Ga}$ ) were estimated according to the model presented in Ref. [15] by applying the linear relation  $T_c = 23 + 181M_t$ . The values found are 928, 930, 758 and 776 K for  $\text{Co}_2\text{MnSi}$ ,  $\text{Co}_2\text{MnGe}$ ,  $\text{Co}_2\text{MnAl}$  and  $\text{Co}_2\text{MnGa}$ , respectively. The  $\text{Co}_2\text{MnGe}$  and  $\text{Co}_2\text{MnSi}$  compounds are of special interest, because of their rather large  $T_c$  values, making them interesting for technological applications. It is clearly seen that the Curie temperature increases as the X atomic number

increases with the same valence number  $Z_t$ , in addition, it is noted that the calculated  $T_c$  value of  $\text{Co}_2\text{MnSi}$  is less than that found experimentally, but in agreement with the results of others as reported in [21,27,28].

### 3.2. Elastic properties and mechanical stability

The elastic constants  $C_{ij}$  contain some of the more important information which can be obtained from ground state total energy calculations. The  $C_{ij}$  can be used to check the phase stability of the studied compounds, and provide an estimation of the strength and indirectly the melting temperature [43]. To obtain the elastic constants of these compounds with cubic structure we have used numerical first principles calculation by computing the components of the stress tensor  $e$  for small strains, using the method reported in ref [44]. It is well known that a cubic crystal has only three independent elastic constants.

The theoretical elastic constants are calculated from the energy variation by applying small strains to the equilibrium lattice configuration. The elastic energy change under strain is given by:

$$\frac{\Delta E}{V} = \frac{V}{2} \sum_{i=1}^6 \sum_{j=1}^6 C_{ij} e_i e_j \quad (1)$$

where  $V$  is the volume of the undistorted lattice cell,  $\Delta E$  is the energy increment by the strain with vector  $e = (e_1, e_2, e_3, e_4, e_5, e_6)$ , and  $C$  is the matrix of elastic constants. The primitive vectors  $a_i$  ( $i = 1, \dots, 3$ ) of crystals are transformed to the new vectors under the strain by

$$\begin{pmatrix} a'_1 \\ a'_2 \\ a'_3 \end{pmatrix} = \begin{pmatrix} a_1 \\ a_2 \\ a_3 \end{pmatrix} \cdot (I + \varepsilon) \quad (2)$$

where  $\varepsilon$  is the strain tensor. It relates to the strain vector  $e$  by

$$\varepsilon = \begin{pmatrix} e_1 & e_6/2 & e_5/2 \\ e_6/2 & e_2 & e_4/2 \\ e_5/2 & e_4/2 & e_3 \end{pmatrix} \quad (3)$$

For the strain under hydrostatic pressure  $e = (\delta, \delta, \delta, 0, 0, 0)$ , which transforms the total energy change into:

$$\frac{\Delta E}{V} = \frac{9}{2} B \delta^2 \quad (4)$$

where  $B$  is the bulk modulus with  $B = (C_{11} + 2C_{12})/3$ .

Under the volume-conserving monoclinic strain  $e = (0, 0, \delta^2/(4 - \delta^2), 0, 0, \delta)$ , the total energy is changed from its initial value as follows:

$$\frac{\Delta E}{V} = \frac{1}{2} C_{44} \delta^2 + O(\delta^4) \quad (5)$$

Finally, for the last type of deformation, we used the volume-conserving rhombohedral strain tensor given by  $e = (0, 0, (1 + \delta)^{-2} - 1, 0, 0, \delta)$  which transforms the total energy to:

$$\frac{\Delta E}{V} = 6C' \delta^2 + O(\delta^3) \quad (6)$$

where  $C'$  is defined by  $C' = (C_{11} - C_{12})/2$ .

In this study, we calculated 21 sets of  $\frac{\Delta E}{V}$  by varying  $\delta$  from  $-0.02$  to  $0.02$  in steps of  $0.002$ . These data are fitted by a quadratic polynomial and then the relevant elastic constant is obtained from the coefficient of the corresponding quadratic term in Eqs. (4)–(6). They are listed in Table 2, together with the data available from experimental and other calculations for comparison [41,45]. Our estimated elastic constants of  $\text{Co}_2\text{MnSi}$  are in excellent agreements with those calculated with the same method incorporated in VASP code by Chen et al [45]. The elastic constants increase as we replace Ge by Si, but they decrease when we replace Ga by Al in  $\text{Co}_2\text{MnX}$  (with  $X = \text{Si, Ge, Al, Ga}$ ) Heusler alloys except for  $C_{44}$ .

Mechanical stability of these compounds has been analyzed in terms of their elastic constants. For cubic crystals, the conditions for mechanical stability are given by [46]:

$$C_{44} > 0, \quad (C_{11} - C_{12})/2 > 0 \quad \text{and} \quad B = (C_{11} + 2C_{12})/3 > 0 \quad (7)$$

From Table 2, we see that these criteria are met, so we conclude that all the compounds in the  $L2_1$  phase are stable.

### 3.3. Electronic and vibrational properties

Spin-polarized band structure calculations for the  $\text{Co}_2\text{MnX}$  (with  $X = \text{Si, Ge, Al, Ga}$ ) Heusler alloys have been investigated. The results for the electronic spectra are in good agreement with the existing calculations reported in the literature [11,16,36,47]. Fig. 2 displays the band structure of  $\text{Co}_2\text{MnX}$  (with  $X = \text{Si, Ge, Al, Ga}$ ). The majority spin band (Fig. 2a, c, e, and g) exhibits metallic character, i.e. the valence band is partially filled, providing conducting electrons at the Fermi level  $E_F$ . The picture is quite different for the minority spin band (Fig. 2b and d), where  $E_F$  is seen to lie within the band gap, which is reminiscent of a semiconductor. We conclude that the Heusler compounds  $\text{Co}_2\text{MnSi}$  and  $\text{Co}_2\text{MnGe}$  show true half-metallicity.

For pure  $\text{Co}_2\text{MnAl}$  and  $\text{Co}_2\text{MnGa}$ , both the majority-spin and minority-spin bands show intersections with the  $E_F$  (see

Fig. 2e–h), showing metallic character for both spin channels. These alloys present a region of very small minority density of states instead of a real gap; so called pseudogap. So, we can conclude that the full Heusler alloys  $\text{Co}_2\text{MnAl}$  and  $\text{Co}_2\text{MnGa}$  show traditional ferromagnetism-false half-metallicity under normal conditions, they are nearly half-metallic. Same result was found by Kübler et al. [36] that the minority spin densities at the Fermi energy nearly vanish for  $\text{Co}_2\text{MnAl}$  and  $\text{Co}_2\text{MnSn}$ . The polarizations at the Fermi level,  $P(E_F)$  are 0.65 and 0.63 for  $\text{Co}_2\text{MnAl}$  and  $\text{Co}_2\text{MnGa}$ , respectively, indicating ferromagnetic character. Generally speaking, one can conclude that there is a close relationship between the magnetic moment and the (HMF) character. The appearance of the gap in the minority density of states constrains the number of minority electrons to be integer. However, an integer value of the magnetic moment may not automatically result in a real gap in the minority or majority density of states.

An important factor for the application of the HMFs is the size of the gap in the minority states and the position of  $E_F$  inside of the gap is also of interest. Small gaps may be easily destroyed by temperature effects. The half-metallicity may also be easily destroyed if  $E_F$  is located close to the band edges, either of the minority valence or conduction bands [48]. Both  $\text{Co}_2\text{MnAl}$  and  $\text{Co}_2\text{MnGa}$  have  $E_F$  outside of the minority band gap. In the case of  $\text{Co}_2\text{MnGe}$ ,  $E_F$  is approximately close to the top of the valence band, whereas for  $\text{Co}_2\text{MnSi}$ , it is inside the gap as shown in Fig. 2b, d, f, and g. At the same time the Fermi energy moves from near the middle of the minority valence states gap ( $\text{Co}_2\text{MnSi}$ ) towards the top of the minority valence band ( $\text{Co}_2\text{MnGe}$ ) then it intersects the valence band of  $\text{Co}_2\text{MnAl}$  and  $\text{Co}_2\text{MnGa}$  compounds. According to Fig. 2b and d the width of the band gap has values in the range of 0.59 to 0.77 eV for  $\text{Co}_2\text{MnGe}$  and  $\text{Co}_2\text{MnSi}$  respectively. The upper valence bands shift towards the Fermi level ( $E_F$ ) when the atomic number increases and they cross  $E_F$  in  $\text{Co}_2\text{MnAl}$  and  $\text{Co}_2\text{MnGa}$  Heusler alloys causing a negative spin flip gap. The spin-flip's values of  $\text{Co}_2\text{MnX}$  Heusler alloys are 0.31, 0.02,  $-0.24$  and  $-0.49$  eV for  $X$  being Si, Ge, Al and Ga, respectively. We conclude that the energy gap and the spin gap of  $\text{Co}_2\text{MnGe}$  and  $\text{Co}_2\text{MnSi}$  increase as the  $X$  atomic number decreases.

For a better understanding of the electronic states, the spin-dependent partial DOS of Co and Mn 3d states are depicted in Fig. 3. While the  $X$  sp orbitals contribute to the bonding states far below the Fermi level, the electronic states around  $E_F$  is dominated by the 3d states of the Mn and Co atoms, and the majority spin states are nearly fully occupied. The DOS curves for the minority spins exhibit two peaks above the Fermi level which are due to both Mn and Co 3d contributions. For minority spin orbitals, we observe that the minority d states of Mn are generally shifted to higher energies compared to the d orbitals of Co due to stronger exchange splitting at the Mn atoms. Hence the two types of d orbitals only partially mix with each other. As evidenced by the integer total magnetic moment of  $5 \mu_B$  per unit cell of  $\text{Co}_2\text{MnSi}$ . Most of the intensity of these unoccupied states comes from Mn d orbitals. In contrast, the states directly above and below the minority spin gap were found to have mostly Co d character.

**Table 2**  
Calculated elastic constants  $C_{ij}$  (GPa) and the curie temperature, for  $\text{Co}_2\text{MnX}$  (with  $X = \text{Si, Ge, Ga, Al}$ ) full-Heusler alloys compared with the available theoretical data.

Material	Reference	$B$ (GPa)	$C_{11}$ (GPa)	$C_{12}$ (GPa)	$C_{44}$ (GPa)	$T_c$ (K)
$\text{Co}_2\text{MnSi}$	This study	213.55	311.16	164.75	153.26	928
	Theoretical [45] [21,27,28]	221	316	174	143	985
$\text{Co}_2\text{MnGe}$	This study	192.69	270.53	153.77	126.55	930
$\text{Co}_2\text{MnAl}$	This study	184.02	264.03	144.02	155.91	758
$\text{Co}_2\text{MnGa}$	This study	184.21	241.44	155.60	132.80	776
	Theoretical [41]	–	–	–	175	–

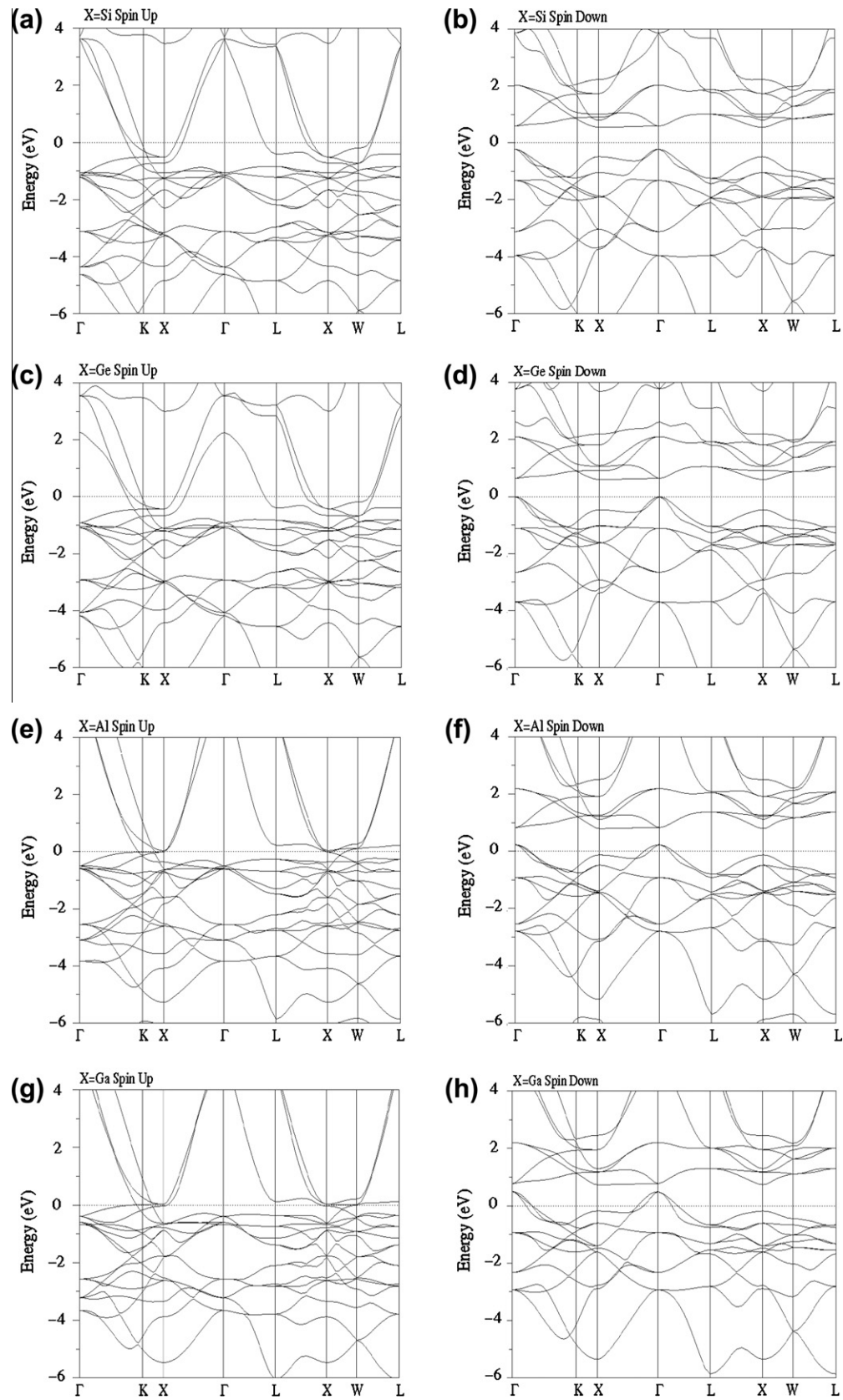


Fig. 2. Calculated electronic band structure of  $\text{Co}_2\text{MnX}$  ( $X = \text{Si}, \text{Ge}, \text{Al}, \text{Ga}$ ) Heusler alloys.

Fig. 4 shows a comparison between the density of states of  $\text{Co}_2\text{MnGa}$  and of  $\text{Co}_2\text{MnAl}$  on one hand and  $\text{Co}_2\text{MnSi}$  and  $\text{Co}_2\text{MnGe}$  on the other hand. The Fermi levels are shown by the dashed

vertical lines in both DOS plots. The overall features are similar in compounds with same  $Z$ , however, it is evident that there are some differences in the DOS of these Heusler alloys due to both

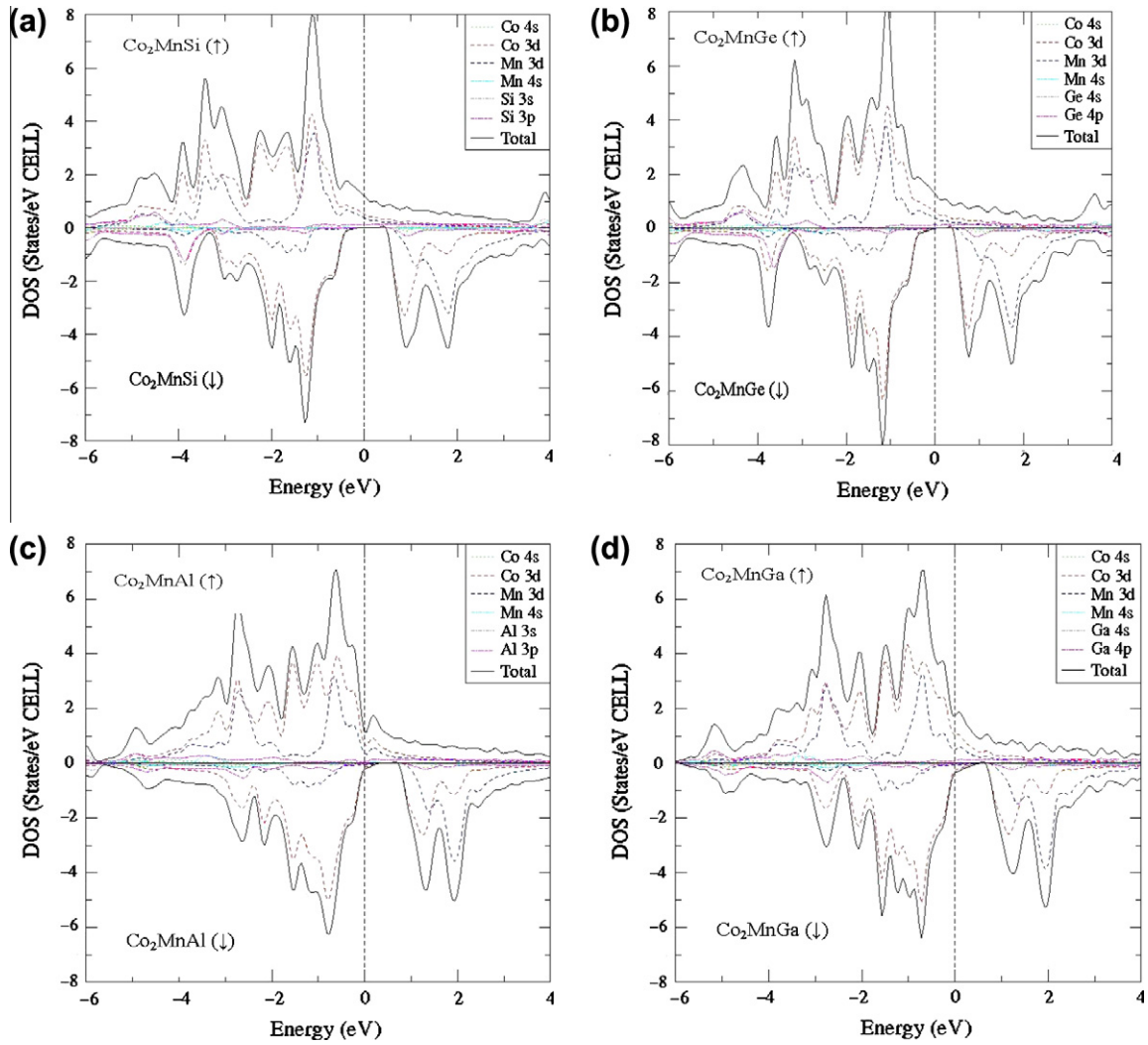


Fig. 3. The total and partial DOS of  $\text{Co}_2\text{MnX}$  ( $X = \text{Si, Ge, Al, Ga}$ ) Heusler alloys.

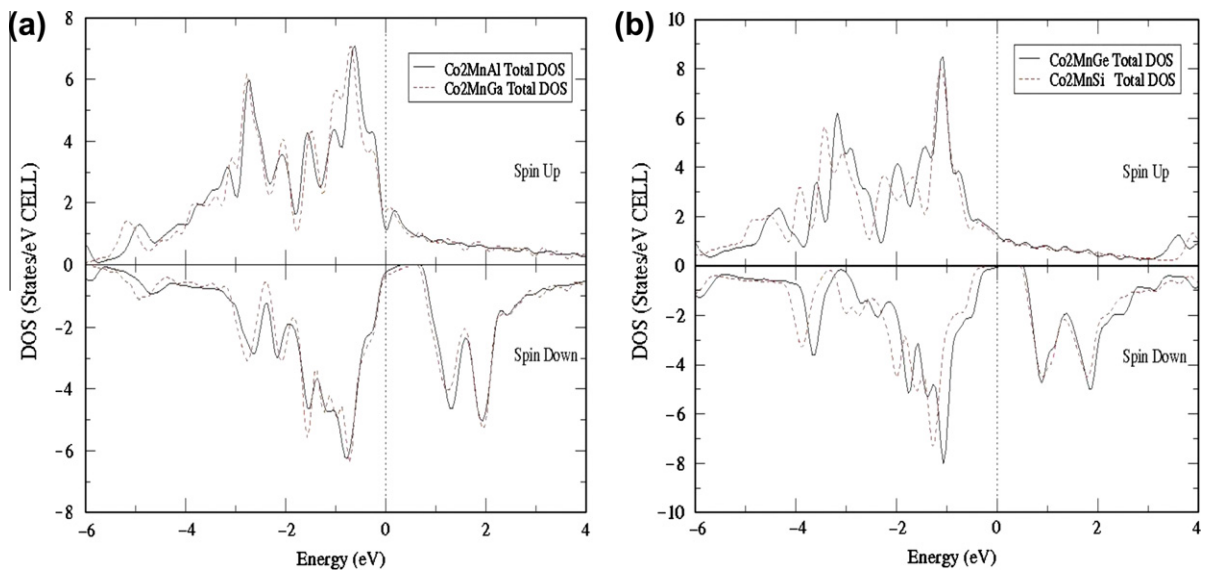
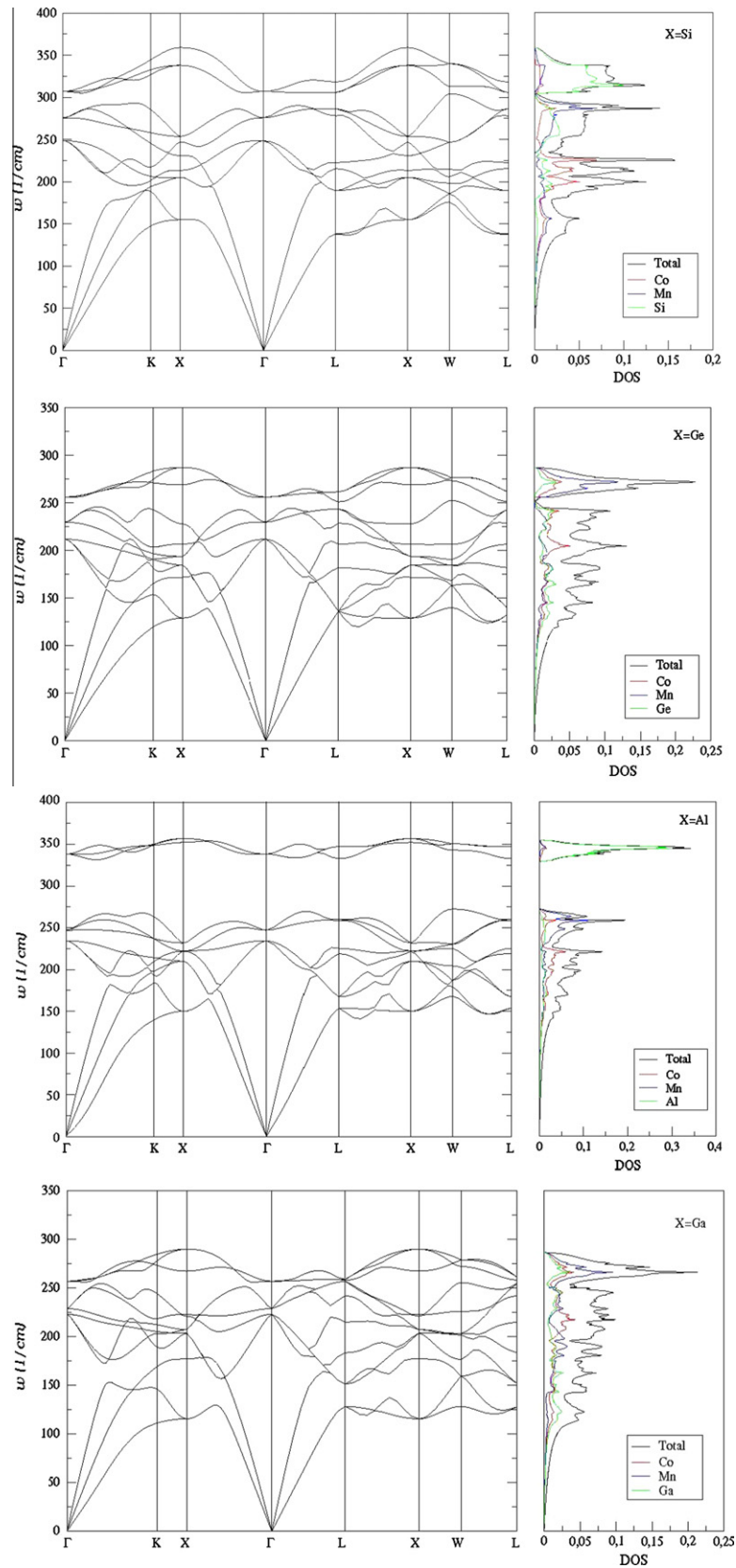


Fig. 4. The effect of atomic number  $X$  on total DOS of (a)  $\text{Co}_2\text{MnSi}$  and  $\text{Co}_2\text{MnGe}$  and (b)  $\text{Co}_2\text{MnAl}$  and  $\text{Co}_2\text{MnGa}$  Heusler alloys.



**Fig. 5.** Calculated phonon dispersion curves and phonon DOS for  $\text{Co}_2\text{MnX}$  ( $X = \text{Si}, \text{Ge}, \text{Al}, \text{Ga}$ ) Heusler alloys along several lines of high symmetry in the Brillouin zone.

the presence of different  $X$  atoms and different volumes. The substitution of the  $X$  atom alters slightly both the position of  $E_F$  and the band gap. The dependence of the electronic structures of the

$\text{Co}_2\text{MnX}$  alloys on the chemical nature of the isoelectronic  $X$  atom has been clearly seen in Fig. 4a and b. All peaks below the Fermi level move to higher energies with increasing lattice parameters

because of the enlarged atomic radii. Because the changes in peak positions upon exchanging the *X* element is proportional to the change in the lattice parameter, the replacement of Si by Ge has bigger consequences than the replacement of Al by Ga.

Our results for the phonon dispersion along the symmetry lines, together with the corresponding partial and total density-of-states, are presented in Fig. 5. Since the unit cell contains four atoms, there are 12 vibrational phonon modes for any chosen *q* point. However, transverse branches are degenerate along certain high-symmetry directions. The absence of any imaginary or negative vibrational mode confirms its dynamical stability. The obtained optical mode frequencies at the zone center ( $\Gamma$ -point) are 248  $\text{cm}^{-1}$ , 275  $\text{cm}^{-1}$  and 307  $\text{cm}^{-1}$  for  $\text{Co}_2\text{MnSi}$ , 212  $\text{cm}^{-1}$ , 229  $\text{cm}^{-1}$  and 256  $\text{cm}^{-1}$  for  $\text{Co}_2\text{MnGe}$ , 234  $\text{cm}^{-1}$ , 246  $\text{cm}^{-1}$  and 338  $\text{cm}^{-1}$  for  $\text{Co}_2\text{MnAl}$ , and 223  $\text{cm}^{-1}$ , 228  $\text{cm}^{-1}$  and 257  $\text{cm}^{-1}$  for  $\text{Co}_2\text{MnGa}$ . The frequencies at the  $\Gamma$ -point for  $\text{Co}_2\text{MnGa}$  and  $\text{Co}_2\text{MnGe}$  are in good agreement with previous first principles calculations of Zayak et al. [42]. The dispersion of the acoustic branches along  $\Gamma$ -*X* symmetry directions for  $\text{Co}_2\text{MnGa}$  and  $\text{Co}_2\text{MnGe}$  also agree well with the theoretical results [42]. The partial phonon density of states shows that the Mn and *X* (Si, Ge, Al, Ga) atoms mainly contribute to the high frequency vibrations because of their lighter atomic masses, while the heavier Co atom dominates the low frequency vibrations. There is significant band gap (59.08  $\text{cm}^{-1}$ ) between the optical and optical phonon modes for  $\text{Co}_2\text{MnAl}$ .  $\text{Co}_2\text{MnSi}$  shows relatively small gap (0.82  $\text{cm}^{-1}$ ) between optical and optical modes.

#### 4. Conclusion

In the present work, we performed the first-principle calculations of the total energy, total and partial density of states, magnetic moments for a series of Co containing bulk Heusler alloys  $\text{Co}_2\text{MnX}$  (with *X* = Si, Ge, Al, Ga). The electronic structure calculations were performed using pseudopotentials. The exchange-correlation functional was evaluated within the GGA, using the Perdew–Burke–Ernzerhof parametrization. We found that the lattice constant increases as we increase the *X* atomic number by 2.1% when substituting Ge for Si and by 0.3% upon substituting Ga for Al. On the other hand the bulk modulus increases by 2.3% when we replace Al by Ga however it decreases when we substitute Ge for Si by about 11.18%. The full Heusler alloys  $\text{Co}_2\text{MnAl}$  and  $\text{Co}_2\text{MnGa}$  have total spin moments 4.06  $\mu_B$  and 4.16  $\mu_B$ , respectively, slightly larger than the ideal 4  $\mu_B$  predicted by the Slater–Pauling rule, while those of the Si and Ge-based alloys are exactly 5  $\mu_B$ . The values of the Curie temperature found are 928, 930, 758 and 776 K for  $\text{Co}_2\text{MnSi}$ ,  $\text{Co}_2\text{MnGe}$ ,  $\text{Co}_2\text{MnAl}$  and  $\text{Co}_2\text{MnGa}$ , respectively. It is clearly seen that the Curie temperature increases as the *X* atomic number increases with the same valence number  $Z_t$ . The elastic constants  $C_{ij}$  are estimated from the energy variation as a function of stress. Elastically, all the compounds have been found to be stable in the  $L2_1$  phase. All  $\text{Co}_2\text{MnX}$  compounds exhibit a gap in the minority states band and are with the exception of  $\text{Co}_2\text{MnAl}$  and  $\text{Co}_2\text{MnGa}$ , clearly half-metallic ferromagnets. The substitution of the *X* atom alters slightly both the position of  $E_F$  and the band gap. The compounds  $\text{Co}_2\text{MnAl}$  and  $\text{Co}_2\text{MnGa}$  are very close to half metallicity. The phonon frequencies and the phonon densities of states in the  $L2_1$  phase in several lines of high symmetry of the Brillouin zone, were obtained and discussed using the density-functional perturbation theory. It seems that  $\text{Co}_2\text{MnAl}$  and  $\text{Co}_2\text{MnGa}$  compounds are less adequate than the  $\text{Co}_2\text{MnSi}$  and  $\text{Co}_2\text{MnGe}$  alloys for realistic spintronic applications.

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